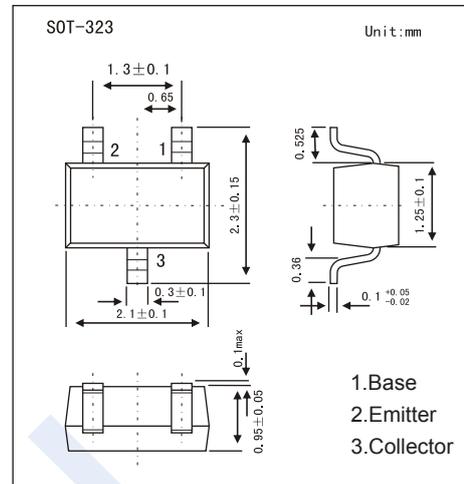


PNP Transistors

MMST3906 (MMST3906)

■ Features

- Epitaxial planar die construction
- Complementary to MMST3904



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-40	V
Collector - Emitter Voltage	V_{CE0}	-40	
Emitter - Base Voltage	V_{EB0}	-5	
Collector Current - Continuous	I_C	-200	mA
Collector Power Dissipation	P_C	200	mW
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	625	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 150	

PNP Transistors

MMST3906 (MMST3906)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CBO}	I _C = -100 μA, I _E = 0	-40			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = -1 mA, I _B = 0	-40			
Emitter - base breakdown voltage	V _{EBO}	I _E = -100 μA, I _C = 0	-5			
Collector-base cut-off current	I _{CBO}	V _{CB} = -40 V, I _E = 0			-100	nA
Collector-emitter cut-off current	I _{CEX}	V _{CE} =-30V, V _{EB(off)} = 3V			-50	
Base cut-off current	I _{BL}	V _{CE} =-30V, V _{EB(off)} = 3V			-50	
Emitter cut-off current	I _{EBO}	V _{EB} = -5V, I _C =0			-100	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-10 mA, I _B =-1mA (Note.1)			-0.2	V
		I _C = -50 mA, I _B = -5mA (Note.1)			-0.3	
Base - emitter saturation voltage	V _{BE(sat)}	I _C =-10 mA, I _B =-1mA (Note.1)	-0.65		-0.85	
		I _C = -50 mA, I _B = -5mA (Note.1)			-0.95	
DC current gain (Note.1)	h _{FE(1)}	V _{CE} = -1V, I _C =- 0.1mA	60			
	h _{FE(2)}	V _{CE} = -1V, I _C = -1mA	80			
	h _{FE(3)}	V _{CE} = -1V, I _C =- 10mA	100		300	
Delay time	t _d	V _{CC} =-3V, V _{BE(off)} =0.5 V, I _C =-10mA			35	nS
Rise time	t _r	I _{B1} =-1 mA			35	
Storage time	t _s	V _{CC} =-3 V, I _C =-10mA, I _{B1} =-I _{B2} =-1mA			225	
Fall time	t _f				75	
Emitter input capacitance	C _{ib}	V _{EB} = -0.5V, I _C = 0, f=1MHz			10	pF
Collector output capacitance	C _{ob}	V _{CB} = -5V, I _E = 0, f=1MHz			4.5	
Transition frequency	f _T	V _{CE} = -20V, I _C = -10mA, f=100MHz	250			MHz

Note.1: Pulse test: pulse width ≤300 μs, duty cycle ≤ 2%.

■ Marking

Marking	K5N
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